

## Product Summary

- Continuous Drain Source Voltage:  $V_{DS} = 60V$
- On-State Resistance: 500m $\Omega$
- Nominal Load Current ( $V_{IN} = 5V$ ): 1.3A
- Clamping Energy: 490mJ

## Description

The ZXMS6004DG is a self protected low side IntelliFET™ MOSFET with logic level input. It integrates over-temperature, over-current, over-voltage (active clamp) and ESD protected logic level functionality. The ZXMS6004DG is ideal as a general purpose switch driven from 3.3V or 5V microcontrollers in harsh environments where standard MOSFETs are not rugged enough.

## Applications

- Especially Suited for Loads with a High In-Rush Current such as Lamps and Motors
- All Types of Resistive, Inductive and Capacitive Loads in Switching Applications
- $\mu C$  Compatible Power Switch for 12V and 24V DC Applications
- Automotive Rated
- Replaces Electromechanical Relays and Discrete Circuits
- Linear Mode Capability - the current-limiting protection circuitry is designed to de-activate at low  $V_{DS}$  to minimize on state power dissipation. The maximum DC operating current is therefore determined by the thermal capability of the package/board combination, rather than by the protection circuitry. This does not compromise the product's ability to self-protect at low  $V_{DS}$ .

## Features and Benefits

- Compact High Power Dissipation Package
- Low Input Current
- Logic Level Input (3.3V and 5V)
- Short Circuit Protection with Auto Restart
- Over Voltage Protection (Active Clamp)
- Thermal Shutdown with Auto Restart
- Over-Current Protection
- Input Protection (ESD)
- High Continuous Current Rating
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **An Automotive-Compliant Part is Available Under Separate Datasheet ([ZXMS6004DGQ](#))**

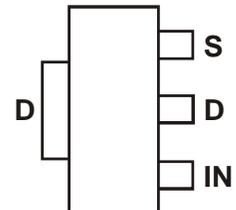
## Mechanical Data

- Case: SOT223 (Type DN)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish (e3)
- Weight: 0.112 grams (Approximate)

SOT223 (Type DN)



Top View



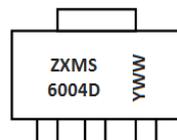
Top View  
Pin Out

## Ordering Information (Note 4)

| Product      | Marking   | Reel Size (inches) | Tape Width (mm) | Quantity per Reel |
|--------------|-----------|--------------------|-----------------|-------------------|
| ZXMS6004DGTA | ZXMS6004D | 7                  | 12              | 1,000             |

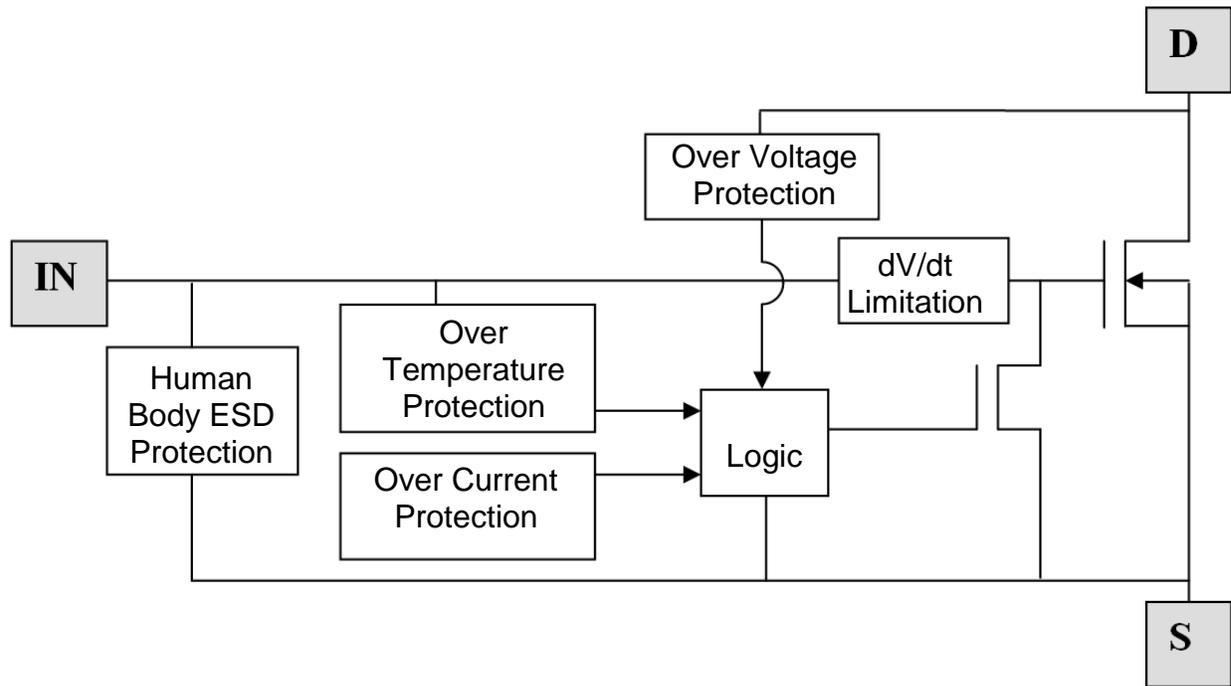
- Notes:
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
  2. See [http://www.diodes.com/quality/lead\\_free/](http://www.diodes.com/quality/lead_free/) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

## Marking Information



ZXMS6004D = Product Type Marking Code  
 YWW = Date Code Marking  
 Y or  $\bar{Y}$  = Last Digit of Year (ex: 8 = 2018)  
 WW or  $\bar{W}$  = Week Code (01 to 53)

## Functional Block Diagram



## Absolute Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise stated.)

| Characteristic  | Symbol              | Value                 | Unit |
|---|---------------------|-----------------------|------|
| Continuous Drain-Source Voltage   | V <sub>DS</sub>     | 60                    | V    |
| Drain-Source Voltage for Short Circuit Protection   | V <sub>DS(SC)</sub> | 36                    | V    |
| Continuous Input Voltage  | V <sub>IN</sub>     | -0.5 to +6            | V    |
| Continuous Input Current @ -0.2V ≤ V <sub>IN</sub> ≤ 6V   | I <sub>IN</sub>     | No Limit              | mA   |
| Continuous Input Current @ V <sub>IN</sub> < -0.2V or V <sub>IN</sub> > 6V                                    | I <sub>IN</sub>     | I <sub>IN</sub>   ≤ 2 | mA   |
| Pulsed Drain Current @ V <sub>IN</sub> = 3.3V   | I <sub>DM</sub>     | 2                     | A    |
| Pulsed Drain Current @ V <sub>IN</sub> = 5V   | I <sub>DM</sub>     | 2.5                   | A    |
| Continuous Source Current (Body Diode) (Note 5)   | I <sub>S</sub>      | 1                     | A    |
| Pulsed Source Current (Body Diode)  | I <sub>SM</sub>     | 5                     | A    |
| Unclamped Single Pulse Inductive Energy, T <sub>J</sub> = +25°C, I <sub>D</sub> = 0.5A, V <sub>DD</sub> = 24V | E <sub>AS</sub>     | 490                   | mJ   |
| Electrostatic Discharge (Human Body Model)  | V <sub>ESD</sub>    | 4000                  | V    |
| Charged Device Model  | V <sub>CDM</sub>    | 1000                  | V    |

## Thermal Resistance

| Characteristic                                       | Symbol           | Value       | Unit  |
|--|------------------|-------------|-------|
| Power Dissipation at T <sub>A</sub> = +25°C (Note 5) | P <sub>D</sub>   | 1.3         | W     |
| Linear Derating Factor                               | P <sub>D</sub>   | 10.4        | mW/°C |
| Power Dissipation at T <sub>A</sub> = +25°C (Note 6) | P <sub>D</sub>   | 3.0         | W     |
| Linear Derating Factor                               | P <sub>D</sub>   | 24          | mW/°C |
| Thermal Resistance, Junction to Ambient (Note 5)     | R <sub>θJA</sub> | 96          | °C/W  |
| Thermal Resistance, Junction to Ambient (Note 6)     | R <sub>θJA</sub> | 42          | °C/W  |
| Thermal Resistance, Junction to Case (Note 7)        | R <sub>θJC</sub> | 12          | °C/W  |
| Operating Temperature Range                          | T <sub>J</sub>   | -40 to +150 | °C    |
| Storage Temperature Range                            | T <sub>STG</sub> | -55 to +150 | °C    |

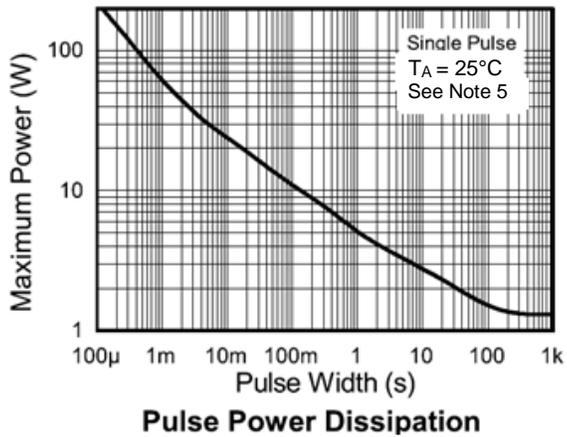
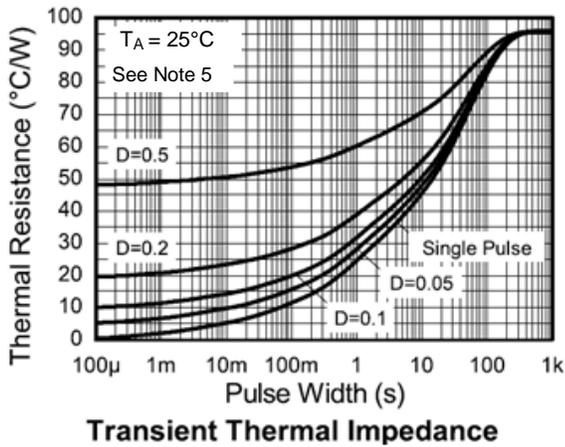
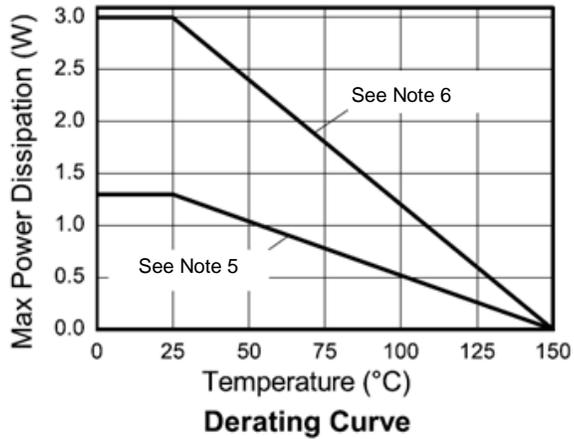
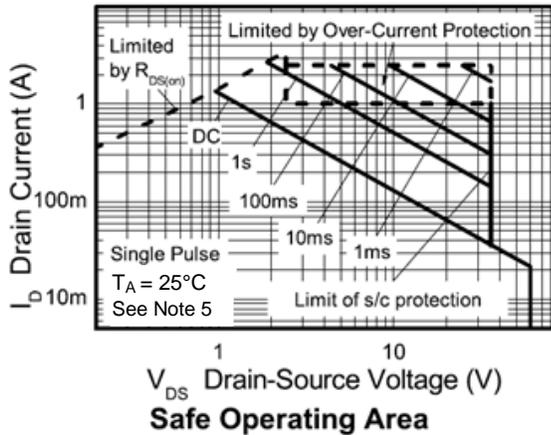
Notes: 5. For a device surface mounted on 15mm x 15mm single sided 1oz weight copper on 1.6mm FR-4 board, in still air conditions.  
6. For a device surface mounted on 50mm x 50mm single sided 2oz weight copper on 1.6mm FR-4 board, in still air conditions.  
7. Thermal resistance between junction and the mounting surfaces of drain and source pins.

## Recommended Operating Conditions

The ZXMS6004DG is optimized for use with  $\mu\text{C}$  operating from 3.3V and 5V supplies.

| Characteristic  | Symbol   | Min | Max  | Unit               |
|---|----------|-----|------|--------------------|
| Input Voltage Range   | $V_{IN}$ | 0   | 5.5  | V                  |
| Ambient Temperature Range                                     | $T_A$    | -40 | +125 | $^{\circ}\text{C}$ |
| High Level Input Voltage for MOSFET to be on                  | $V_{IH}$ | 3   | 5.5  | V                  |
| Low Level Input Voltage for MOSFET to be off                  | $V_{IL}$ | 0   | 0.7  | V                  |
| Peripheral Supply Voltage (Voltage to Which Load is Referred) | $V_P$    | 0   | 36   | V                  |

## Thermal Characteristics

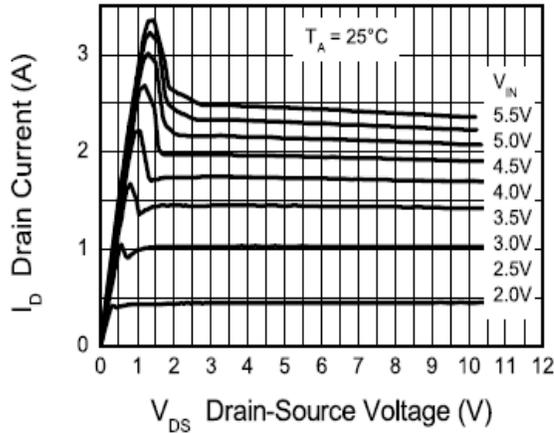


**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise stated.)

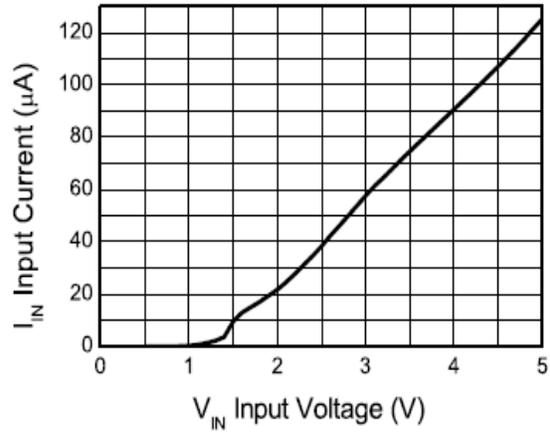
| Characteristic                              | Symbol              | Min  | Typ  | Max | Unit | Test Condition  |
|---|---------------------|------|------|-----|------|---|
| <b>Static Characteristics</b>               |                     |      |      |     |      |   |
| Drain-Source Clamp Voltage                  | V <sub>DS(AZ)</sub> | 60   | 65   | 70  | V    | I <sub>D</sub> = 10mA   |
| Off State Drain Current                     | I <sub>DSS</sub>    | –    | –    | 0.5 | μA   | V <sub>DS</sub> = 12V, V <sub>IN</sub> = 0V                           |
|   |                     | –    | –    | 1   |      | V <sub>DS</sub> = 36V, V <sub>IN</sub> = 0V                           |
| Input Threshold Voltage                     | V <sub>IN(TH)</sub> | 0.7  | 1.2  | 1.5 | V    | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 1mA              |
| Input Current                               | I <sub>IN</sub>     | –    | 60   | 100 | μA   | V <sub>IN</sub> = 3V  |
|   |                     | –    | 120  | 200 |      | V <sub>IN</sub> = 5V  |
| Input Current While Over Temperature Active | –                   | –    | –    | 400 | μA   | V <sub>IN</sub> = 5V  |
| Static Drain-Source On-State Resistance     | R <sub>DS(ON)</sub> | –    | 400  | 600 | mΩ   | V <sub>IN</sub> = 3V, I <sub>D</sub> = 0.5A                           |
|   |                     | –    | 350  | 500 |      | V <sub>IN</sub> = 5V, I <sub>D</sub> = 0.5A                           |
| Continuous Drain Current (Note 5)           | I <sub>D</sub>      | 0.9  | –    | –   | A    | V <sub>IN</sub> = 3V; T <sub>A</sub> = +25°C                          |
|   |                     | 1.0  | –    | –   |      | V <sub>IN</sub> = 5V; T <sub>A</sub> = +25°C                          |
| Continuous Drain Current (Note 6)           | I <sub>D</sub>      | 1.2  | –    | –   | A    | V <sub>IN</sub> = 3V; T <sub>A</sub> = +25°C                          |
|   |                     | 1.3  | –    | –   |      | V <sub>IN</sub> = 5V; T <sub>A</sub> = +25°C                          |
| Current Limit (Note 8)                      | I <sub>D(LIM)</sub> | 0.7  | 1.7  | –   | A    | V <sub>IN</sub> = 3V  |
|   |                     | 1    | 2.2  | –   |      | V <sub>IN</sub> = 5V  |
| <b>Dynamic Characteristics</b>              |                     |      |      |     |      |   |
| Turn On Delay Time                          | t <sub>D(ON)</sub>  | –    | 5    | –   | μs   | V <sub>DD</sub> = 12V, I <sub>D</sub> = 0.5A,<br>V <sub>GS</sub> = 5V |
| Rise Time                                   | t <sub>R</sub>      | –    | 10   | –   |      |   |
| Turn Off Delay Time                         | t <sub>D(OFF)</sub> | –    | 45   | –   |      |   |
| Fall Time                                   | t <sub>F</sub>      | –    | 15   | –   |      |   |
| <b>Over-Temperature Protection</b>          |                     |      |      |     |      |   |
| Thermal Overload Trip Temperature (Note 9)  | T <sub>JT</sub>     | +150 | +175 | –   | °C   | –   |
| Thermal Hysteresis (Note 9)                 | –                   | –    | +10  | –   | °C   | –   |

- Notes:
- The drain current is restricted only when the device is in saturation (see graph 'typical output characteristic'). This allows the device to be used in the fully on state without interference from the current limit. The device is fully protected at all drain currents, as the low power dissipation generated outside saturation makes current limit unnecessary.
  - Over-temperature protection is designed to prevent device destruction under fault conditions. Fault conditions are considered as "outside" normal operating range, so this part is not designed to withstand over-temperature for extended periods.

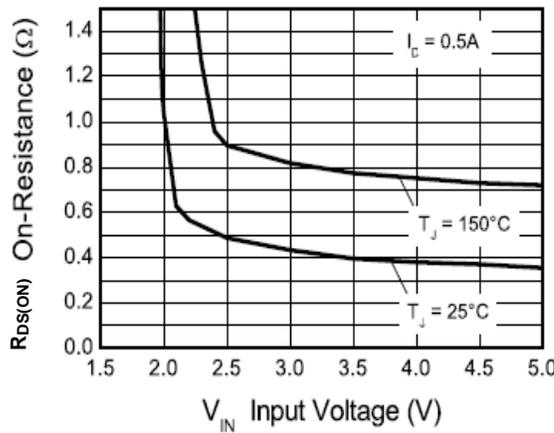
**Typical Characteristics**



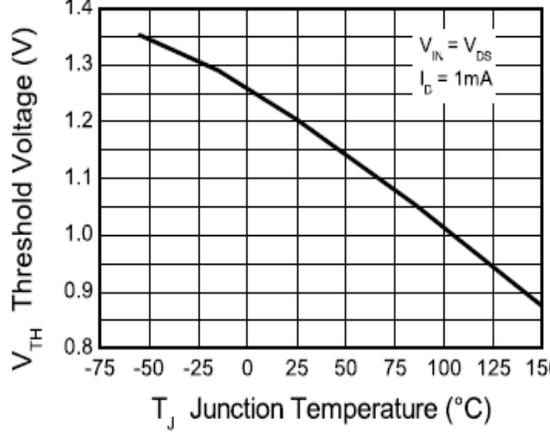
**Typical Output Characteristic**



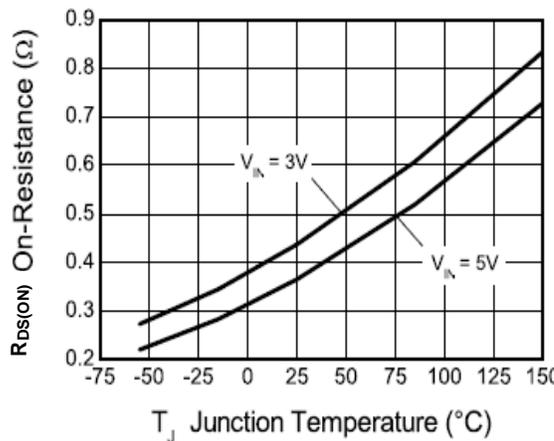
**Input Current vs Input Voltage**



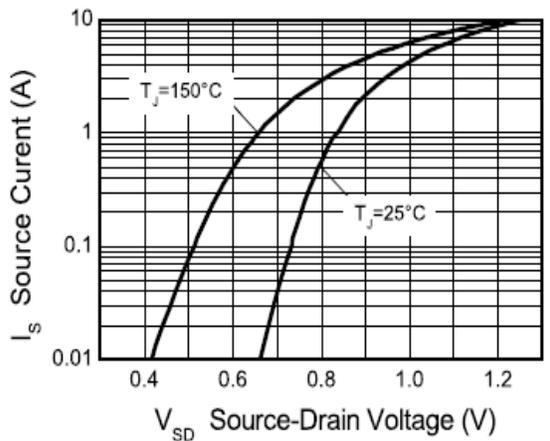
**On-Resistance vs Input Voltage**



**Threshold Voltage vs Temperature**

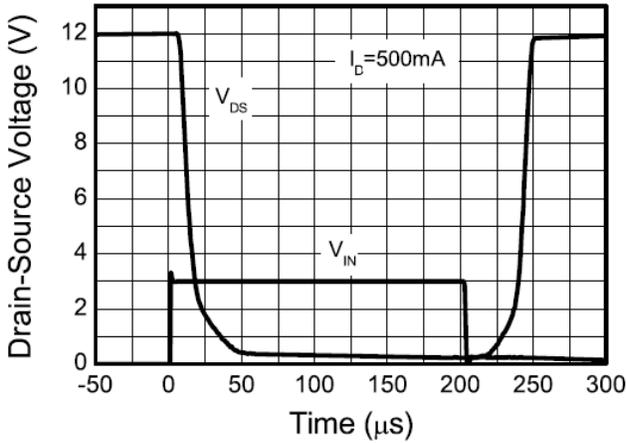


**On-Resistance vs Temperature**

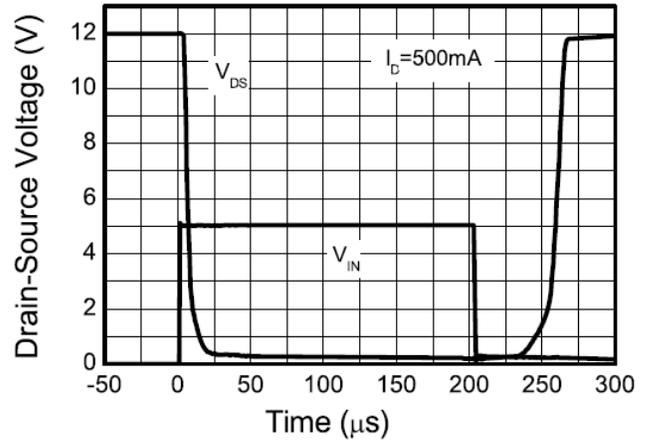


**Reverse Diode Characteristic**

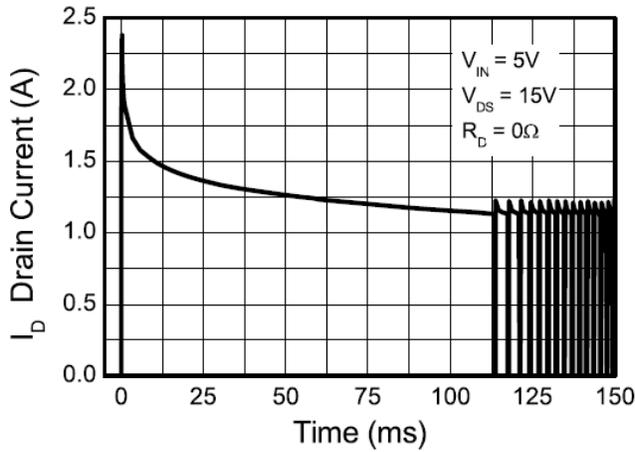
**Typical Characteristics (Cont.)**



**Switching Speed**



**Switching Speed**

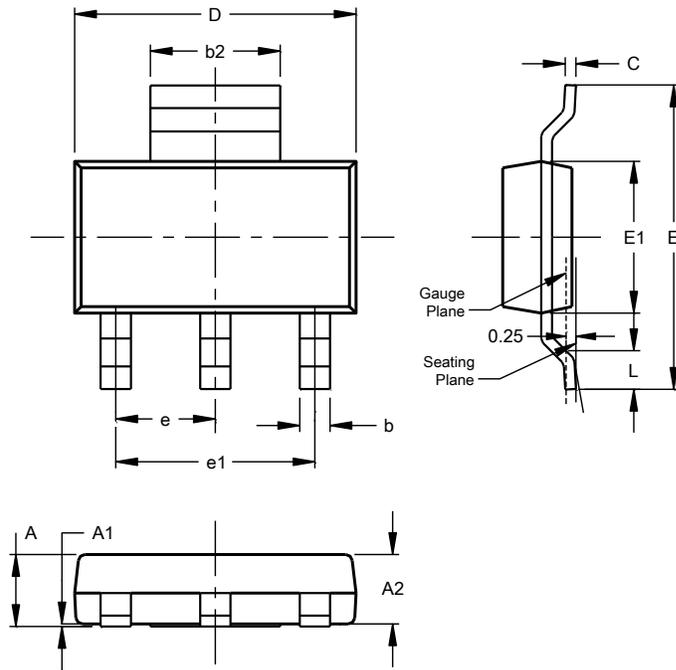


**Typical Short Circuit Protection**

**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**SOT223 (Type DN)**

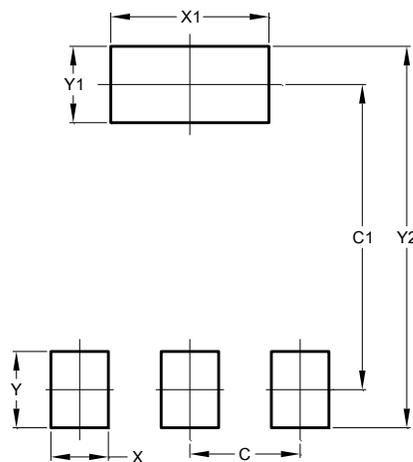


| SOT223 (Type DN)     |      |      |      |
|----------------------|------|------|------|
| Dim                  | Min  | Max  | Typ  |
| A                    | --   | 1.70 | --   |
| A1                   | 0.01 | 0.15 | --   |
| A2                   | 1.50 | 1.68 | 1.60 |
| b                    | 0.60 | 0.80 | 0.70 |
| b2                   | 2.90 | 3.10 | --   |
| c                    | 0.20 | 0.32 | --   |
| D                    | 6.30 | 6.70 | --   |
| E                    | 6.70 | 7.30 | --   |
| E1                   | 3.30 | 3.70 | --   |
| e                    | --   | --   | 2.30 |
| e1                   | --   | --   | 4.60 |
| L                    | 0.85 | --   | --   |
| All Dimensions in mm |      |      |      |

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**SOT223 (Type DN)**



| Dimensions | Value (in mm) |
|------------|---------------|
| C          | 2.30          |
| C1         | 6.40          |
| X          | 1.20          |
| X1         | 3.30          |
| Y          | 1.60          |
| Y1         | 1.60          |
| Y2         | 8.00          |

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